

NID6002N

Preferred Device

Self-Protected FET with Temperature and Current Limit

65 V, 6.5 A, Single N-Channel, DPAK

HDPlus™ devices are an advanced series of power MOSFETs which utilize ON Semiconductor's latest MOSFET technology process to achieve the lowest possible on-resistance per silicon area while incorporating smart features. Integrated thermal and current limits work together to provide short circuit protection. The devices feature an integrated Drain-to-Gate Clamp that enables them to withstand high energy in the avalanche mode. The Clamp also provides additional safety margin against unexpected voltage transients. Electrostatic Discharge (ESD) protection is provided by an integrated Gate-to-Source Clamp.

Features

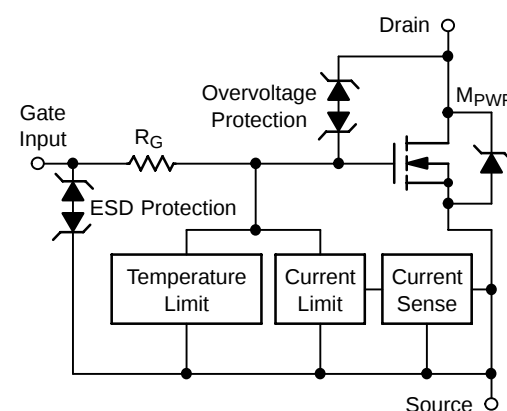
- Short Circuit Protection/Current Limit
- Thermal Shutdown with Automatic Restart
- I_{DSS} Specified at Elevated Temperature
- Avalanche Energy Specified
- Slew Rate Control for Low Noise Switching
- Overvoltage Clamped Protection
- Pb-Free Package is Available



ON Semiconductor®

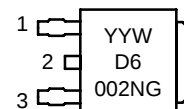
<http://onsemi.com>

V_{DS} (Clamped)	$R_{DS(on)}$ TYP	I_D TYP (Limited)
65 V	210 mΩ	6.5 A



DPAK
CASE 369C
STYLE 2

MARKING DIAGRAM



D6002N = Device Code
Y = Year
WW = Work Week
G = Pb-Free Device

1 = Gate
2 = Drain
3 = Source

ORDERING INFORMATION

Device	Package	Shipping [†]
NID6002NT4	DPAK	2500/Tape & Reel
NID6002NT4G	DPAK (Pb-Free)	2500/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

NID6002N

MOSFET MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage Internally Clamped	V_{DSS}	70	Vdc
Gate-to-Source Voltage	V_{GS}	± 14	Vdc
Drain Current Continuous	I_D	Internally Limited	
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ (Note 1) @ $T_A = 25^\circ\text{C}$ (Note 2)	P_D	1.3 2.5	W
Thermal Resistance Junction-to-Case Junction-to-Ambient (Note 1) Junction-to-Ambient (Note 2)	$R_{\theta JC}$ $R_{\theta JA}$ $R_{\theta JA}$	3.0 95 50	$^\circ\text{C/W}$
Single Pulse Drain-to-Source Avalanche Energy ($V_{DD} = 50\text{ Vdc}$, $V_{GS} = 5.0\text{ Vdc}$, $I_L = 1.3\text{ Apk}$, $L = 160\text{ mH}$, $R_G = 25\ \Omega$) (Note 3)	E_{AS}	143	mJ
Operating and Storage Temperature Range (Note 4)	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted onto minimum pad size (100 sq/mm) FR4 PCB, 1 oz cu.
2. Mounted onto 1" square pad size (700 sq/mm) FR4 PCB, 1 oz cu.
3. Not subject to production test.
4. Normal pre-fault operating range. See thermal limit range conditions.

NID6002N

MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Clamped Breakdown Voltage (V _{GS} = 0 V, I _D = 2 mA)	V _{(BR)DSS}	60	65	70	V
Zero Gate Voltage Drain Current (V _{DS} = 52 V, V _{GS} = 0 V)	I _{DSS}	–	27	100	μA
Gate Input Current (V _{GS} = 5.0 V, V _{DS} = 0 V)	I _{GSS}	–	45	200	μA

ON CHARACTERISTICS

Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 150 μA) Threshold Temperature Coefficient	V _{GS(th)}	1.0 –	1.85 5.0	2.4 –	V –mV/°C
Static Drain-to-Source On-Resistance (Note 5) (V _{GS} = 10 V, I _D = 2.0 A, T _J @ 25°C)	R _{DS(on)}	–	185	210	mΩ
Static Drain-to-Source On-Resistance (Note 5) (V _{GS} = 5.0 V, I _D = 2.0 A, T _J @ 25°C) (V _{GS} = 5.0 V, I _D = 2.0 A, T _J @ 150°C)	R _{DS(on)}	– –	210 445	240 520	mΩ
Source-Drain Forward On Voltage (I _S = 7.0 A, V _{GS} = 0 V)	V _{SD}	–	0.9	1.1	V

SWITCHING CHARACTERISTICS (Note 8)

Turn-on Delay Time	R _L = 6.6 Ω, V _{in} = 0 to 10 V, V _{DD} = 13.8 V, I _D = 2.0 A, 10% V _{in} to 10% I _D	t _{d(on)}	–	96	–	ns
Turn-on Rise Time	R _L = 6.6 Ω, V _{in} = 0 to 10 V, V _{DD} = 13.8 V, I _D = 2.0 A, 10% I _D to 90% I _D	t _{rise}	–	250	–	ns
Turn-off Delay Time	R _L = 6.6 Ω, V _{in} = 0 to 10 V, V _{DD} = 13.8 V, I _D = 2.0 A, 90% V _{in} to 90% I _D	t _{d(off)}	–	840	–	ns
Turn-off Fall Time	R _L = 6.6 Ω, V _{in} = 0 to 10 V, V _{DD} = 13.8 V, I _D = 2.0 A, 90% I _D to 10% I _D	t _{fall}	–	660	–	ns
Slew Rate ON	R _L = 6.6 Ω, V _{in} = 0 to 10 V, V _{DD} = 13.8 V, I _D = 2.0 A, 70% to 50% V _{DD}	dV _{DS} /dT _{on}	–	73	–	V/μs
Slew Rate OFF	R _L = 6.6 Ω, V _{in} = 0 to 10 V, V _{DD} = 13.8 V, I _D = 2.0 A, 50% to 70% V _{DD}	dV _{DS} /dT _{off}	–	35	–	V/μs

SELF PROTECTION CHARACTERISTICS (Note 6)

Current Limit	V _{DS} = 10 V, V _{GS} = 5.0 V, T _J = 25°C (Note 7) V _{DS} = 10 V, V _{GS} = 5.0 V, T _J = 130°C (Notes 7, 8) V _{DS} = 10 V, V _{GS} = 10 V, T _J = 25°C (Notes 7, 8)	I _{LIM}	4.0 4.0 –	6.4 5.5 7.9	11 11 –	A
Temperature Limit (Turn-off)	V _{GS} = 5.0 V (Note 8)	T _{LIM(off)}	150	180	200	°C
Thermal Hysteresis	V _{GS} = 5.0 V	ΔT _{LIM(on)}	–	10	–	°C
Temperature Limit (Turn-off)	V _{GS} = 10 V (Note 8)	T _{LIM(off)}	150	180	200	°C
Thermal Hysteresis	V _{GS} = 10 V	ΔT _{LIM(on)}	–	20	–	°C
Input Current during Thermal Fault	V _{DS} = 0 V, V _{GS} = 5.0 V, T _J = T _J > T _(fault) (Note 8) V _{DS} = 0 V, V _{GS} = 10 V, T _J = T _J > T _(fault) (Note 8)	I _{g(fault)}	5.5 12	5.2 11	–	mA

ESD ELECTRICAL CHARACTERISTICS

Electro-Static Discharge Capability Human Body Model (HBM) Machine Model (MM)	ESD	8000 400	– –	– –	V
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- Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
- Fault conditions are viewed as beyond the normal operating range of the part.
- Current limit measured at 380 μs after gate pulse.
- Not subject to production test.

TYPICAL PERFORMANCE CURVES

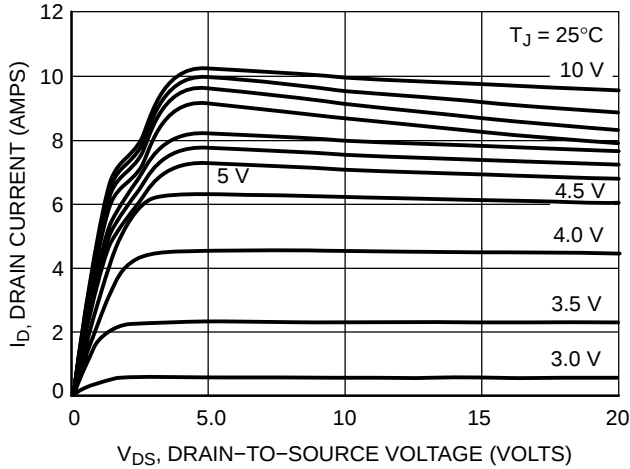


Figure 1. On-Region Characteristics

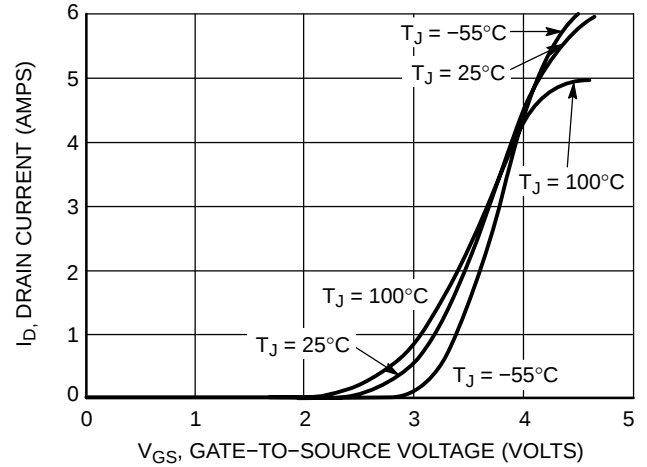


Figure 2. Transfer Characteristics

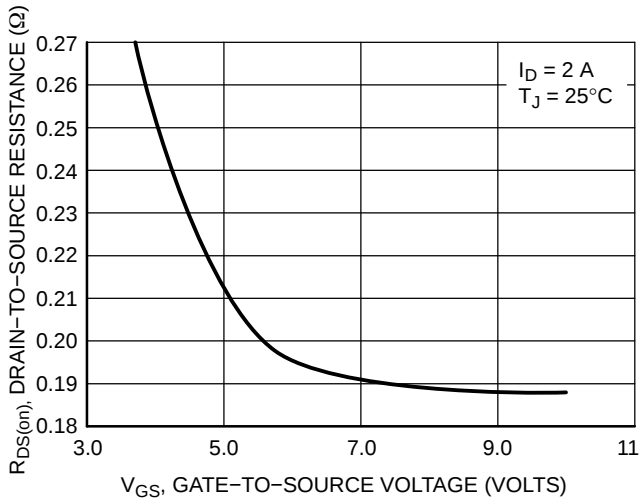


Figure 3. On-Resistance vs. Gate-to-Source Voltage

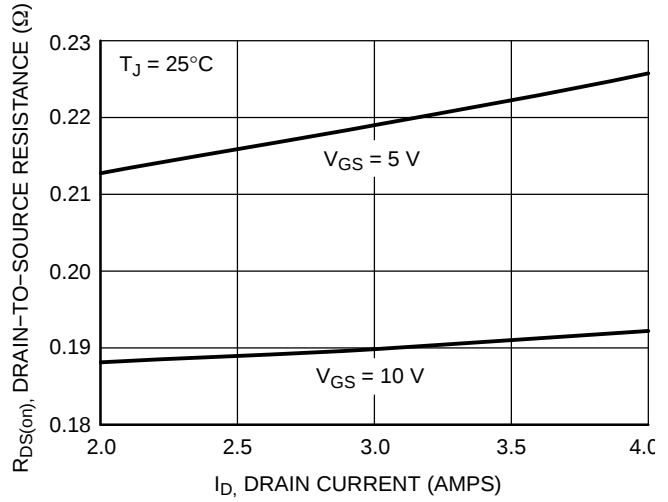


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

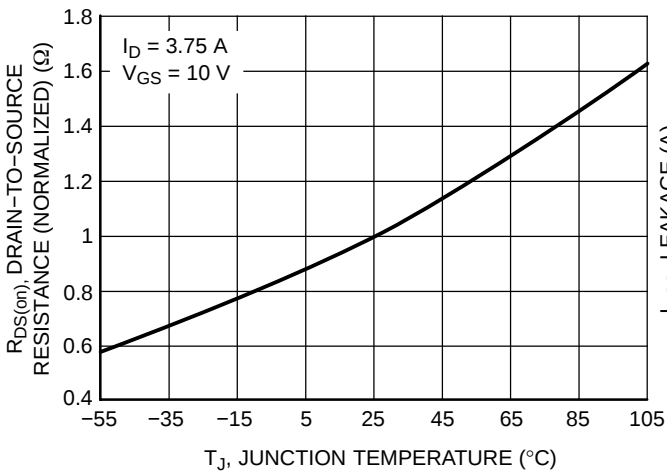


Figure 5. On-Resistance Variation with Temperature

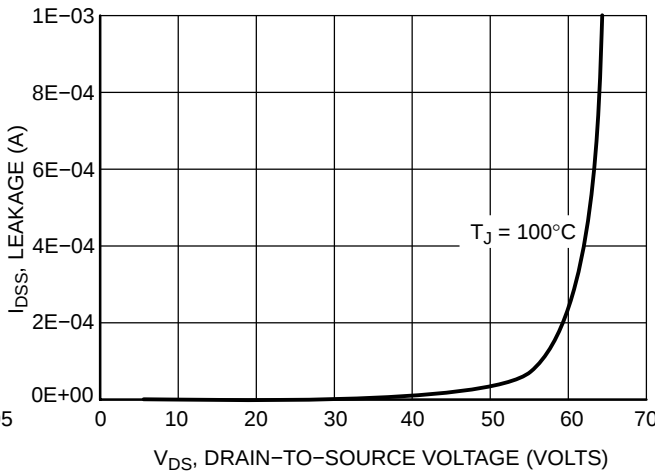


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES

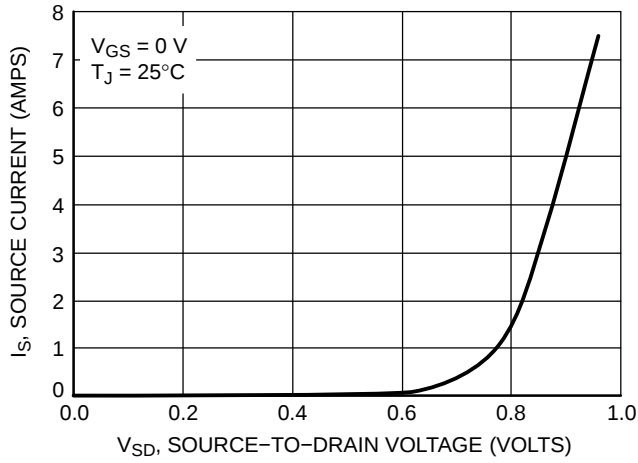


Figure 7. Diode Forward Voltage vs. Current

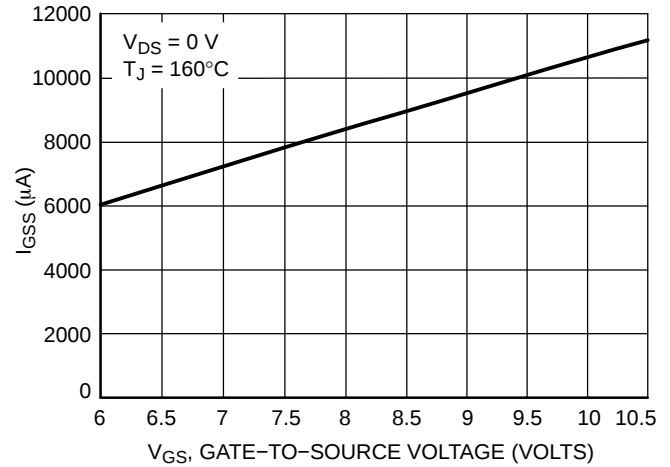


Figure 8. Input Current vs. Gate Voltage

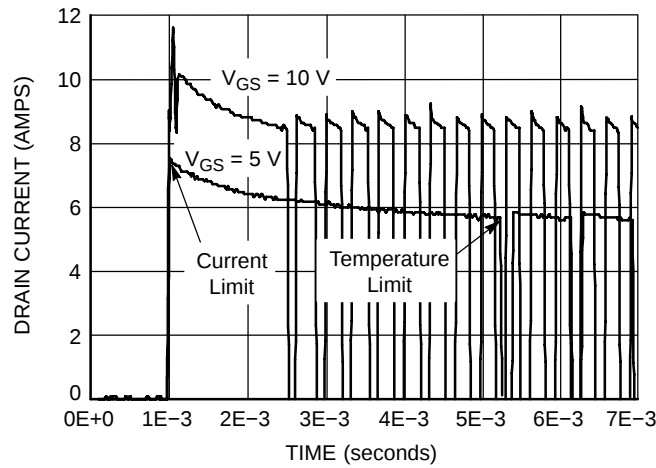
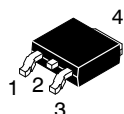


Figure 9. Short Circuit Response*

*(Actual thermal cycling response in short circuit dependent on device power level, thermal mounting, and ambient temperature conditions)

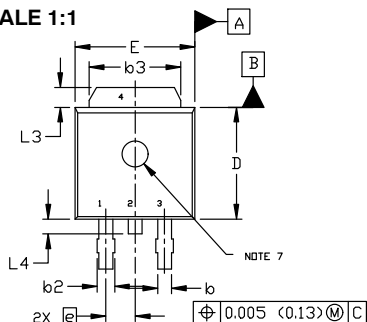
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



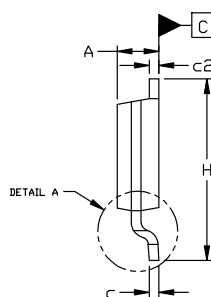
DPAK (SINGLE GAUGE) CASE 369C ISSUE G

DATE 31 MAY 2023

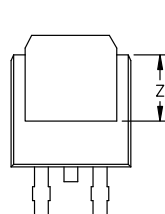
SCALE 1:1



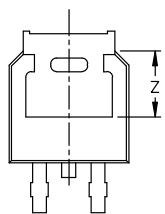
TOP VIEW



SIDE VIEW

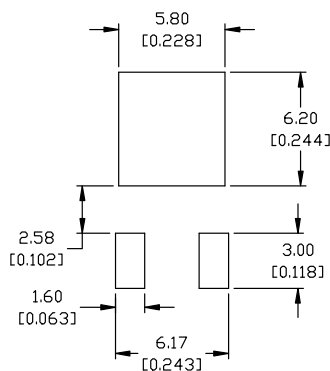


BOTTOM VIEW



BOTTOM VIEW

ALTERNATE
CONSTRUCTIONS



RECOMMENDED MOUNTING FOOTPRINT*

*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLE 1:

PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:

PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:

PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:

PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:

PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:

PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:

PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 8:

PIN 1. N/C
2. CATHODE
3. ANODE
4. CATHODE

STYLE 9:

PIN 1. ANODE
2. CATHODE
3. RESISTOR ADJUST
4. CATHODE

STYLE 10:

PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

NOTES:

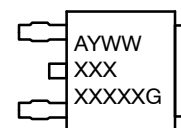
1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29	BSC
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4	----	0.040	---	1.01
Z	0.155	----	3.93	---

GENERIC MARKING DIAGRAM*



IC



Discrete

XXXXXX = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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